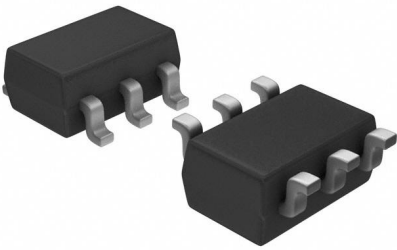


# XN0438100L Datasheet

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<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	XN0438100L-DG
Manufacturer	<a href="#">Panasonic Electronic Components</a>
Manufacturer Product Number	XN0438100L
Description	TRANS NPN/PNP PREBIAS 0.3W MINI6
Detailed Description	Pre-Biased Bipolar Transistor (BJT) 1 NPN, 1 PNP - P re-Biased (Dual) 50V 100mA, 500mA 150MHz, 200M Hz 300mW Surface Mount MINI6-G1



Tel: +00 852-30501935

RFQ Email: [Info@DiGi-Electronics.com](mailto:Info@DiGi-Electronics.com)

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## Purchase and inquiry

Manufacturer Product Number:

XN0438100L

Series:

-

Transistor Type:

1 NPN, 1 PNP - Pre-Biased (Dual)

Voltage - Collector Emitter Breakdown (Max):

50V

Resistor - Emitter Base (R2):

4.7kOhms

Vce Saturation (Max) @ Ib, Ic:

250mV @ 300µA, 10mA / 250mV @ 5mA, 100mA

Frequency - Transition:

150MHz, 200MHz

Mounting Type:

Surface Mount

Supplier Device Package:

MINI6-G1

Manufacturer:

Panasonic Electronic Components

Product Status:

Obsolete

Current - Collector (Ic) (Max):

100mA, 500mA

Resistor - Base (R1):

47kOhms, 4.7kOhms

DC Current Gain (hFE) (Min) @ Ic, Vce:

80 @ 5mA, 10V / 50 @ 100mA, 10V

Current - Collector Cutoff (Max):

500nA, 1µA

Power - Max:

300mW

Package / Case:

SOT-23-6

Base Product Number:

XN0438

## Environmental & Export classification

Moisture Sensitivity Level (MSL):

1 (Unlimited)

HTSUS:

8541.21.0075

ECCN:

EAR99

# XN04381 (XN4381)

Silicon NPN epitaxial planar type (Tr1)  
 Silicon PNP epitaxial planar type (Tr2)

For switching/digital circuits

## ■ Features

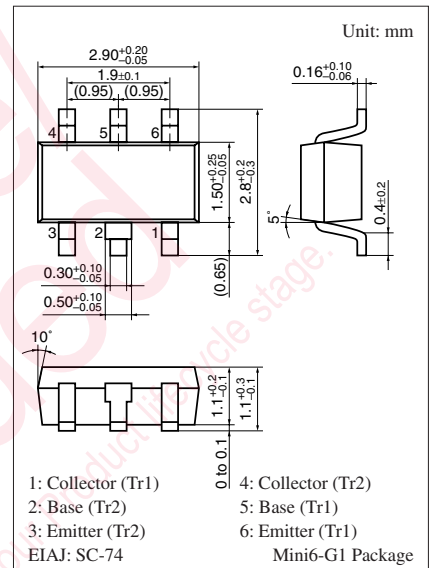
- Two elements incorporated into one package  
 (Transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half

## ■ Basic Part Number

- UNR2213 (UN2213) + UNR2122 (UN2122)

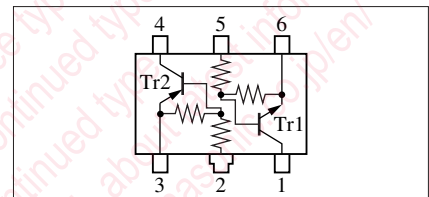
## ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

	Parameter	Symbol	Rating	Unit
Tr1	Collector-base voltage (Emitter open)	$V_{CBO}$	50	V
	Collector-emitter voltage (Base open)	$V_{CEO}$	50	V
	Collector current	$I_C$	100	mA
Tr2	Collector-base voltage (Emitter open)	$V_{CBO}$	-50	V
	Collector-emitter voltage (Base open)	$V_{CEO}$	-50	V
	Collector current	$I_C$	-500	mA
Overall	Total power dissipation	$P_T$	300	mW
	Junction temperature	$T_j$	150	$^\circ\text{C}$
	Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$



Marking Symbol: CW

Internal Connection



Note) The part number in the parenthesis shows conventional part number.



■ Electrical Characteristics  $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

• Tr1

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = 10 \mu\text{A}, I_E = 0$	50			V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = 2 \text{ mA}, I_B = 0$	50			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 50 \text{ V}, I_E = 0$			0.1	$\mu\text{A}$
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = 50 \text{ V}, I_B = 0$			0.5	$\mu\text{A}$
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = 6 \text{ V}, I_C = 0$			0.1	mA
Forward current transfer ratio	$h_{FE}$	$V_{CE} = 10 \text{ V}, I_C = 5 \text{ mA}$	80			—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10 \text{ mA}, I_B = 0.3 \text{ mA}$			0.25	V
Output voltage high-level	$V_{OH}$	$V_{CC} = 5 \text{ V}, V_B = 0.5 \text{ V}, R_L = 1 \text{ k}\Omega$	4.9			V
Output voltage low-level	$V_{OL}$	$V_{CC} = 5 \text{ V}, V_B = 3.5 \text{ V}, R_L = 1 \text{ k}\Omega$			0.2	V
Input resistance	$R_1$		-30%	47	+30%	k $\Omega$
Resistance ratio	$R_1 / R_2$		0.8	1.0	1.2	—
Transition frequency	$f_T$	$V_{CB} = 10 \text{ V}, I_E = -2 \text{ mA}, f = 200 \text{ MHz}$		150		MHz

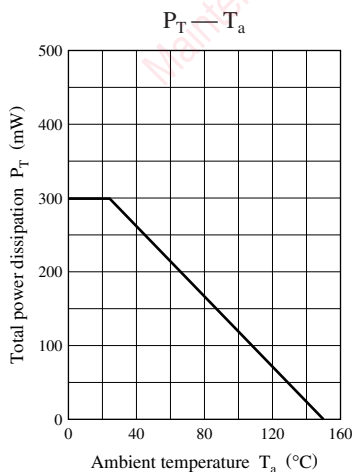
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

• Tr2

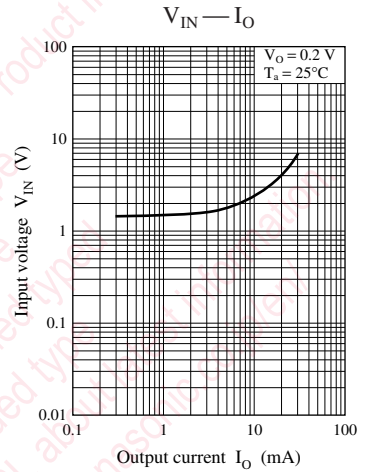
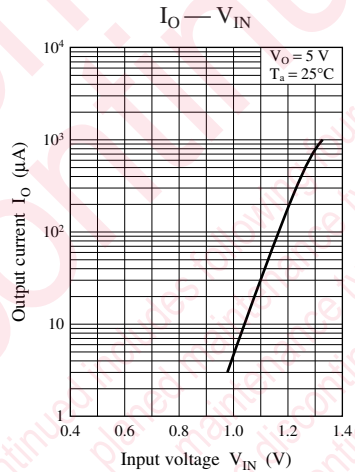
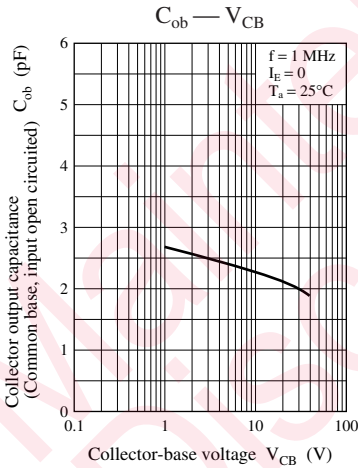
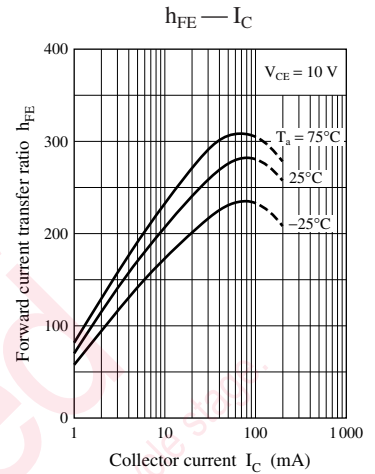
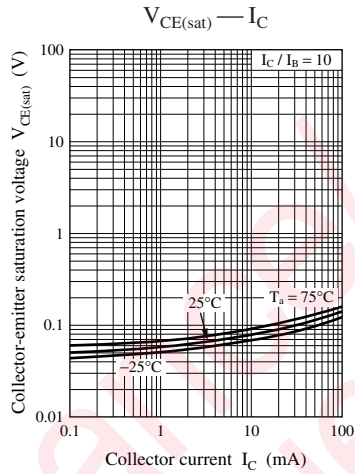
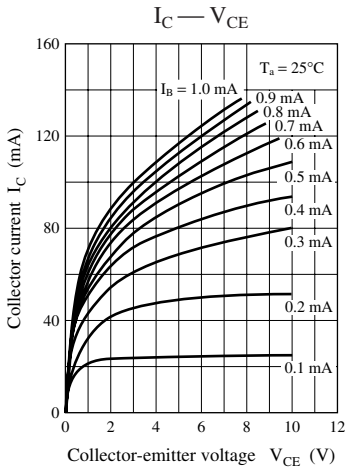
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = -10 \mu\text{A}, I_E = 0$	-50			V
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = -2 \text{ mA}, I_B = 0$	-50			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = -50 \text{ V}, I_E = 0$			-1	$\mu\text{A}$
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = -50 \text{ V}, I_B = 0$			-1	$\mu\text{A}$
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = -6 \text{ V}, I_C = 0$			-2	mA
Forward current transfer ratio	$h_{FE}$	$V_{CE} = -10 \text{ V}, I_C = -100 \text{ mA}$	50			—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100 \text{ mA}, I_B = -5 \text{ mA}$			-0.25	V
Output voltage high-level	$V_{OH}$	$V_{CC} = -5 \text{ V}, V_B = -0.5 \text{ V}, R_L = 500 \Omega$	-4.9			V
Output voltage low-level	$V_{OL}$	$V_{CC} = -5 \text{ V}, V_B = -3.5 \text{ V}, R_L = 500 \Omega$			-0.2	V
Input resistance	$R_1$		-30%	4.7	+30%	k $\Omega$
Resistance ratio	$R_1 / R_2$		0.8	1.0	1.2	—
Transition frequency	$f_T$	$V_{CB} = -10 \text{ V}, I_E = 50 \text{ mA}, f = 200 \text{ MHz}$		200		MHz

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

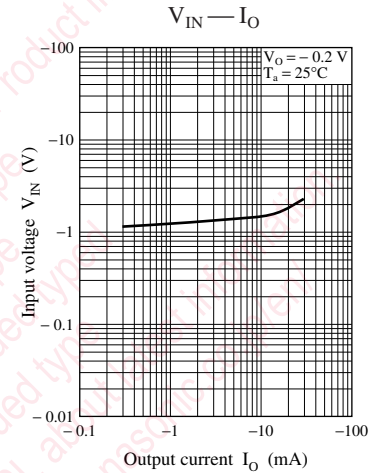
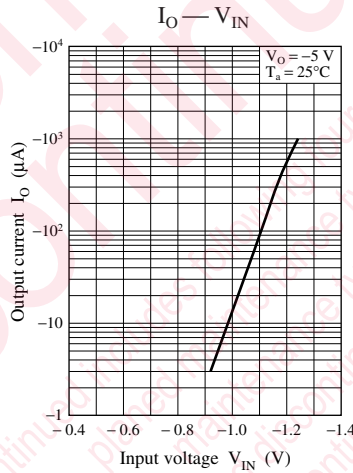
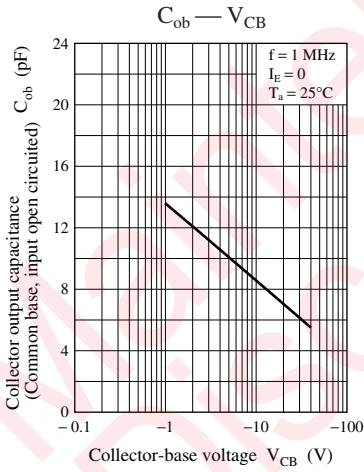
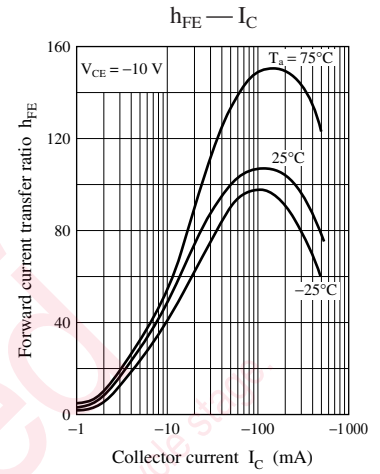
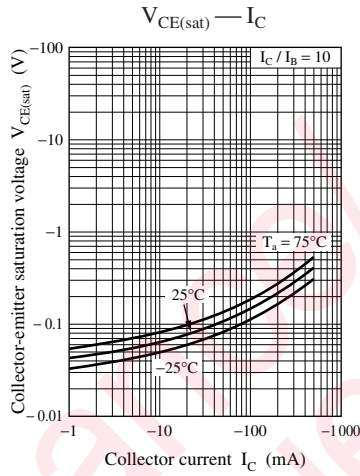
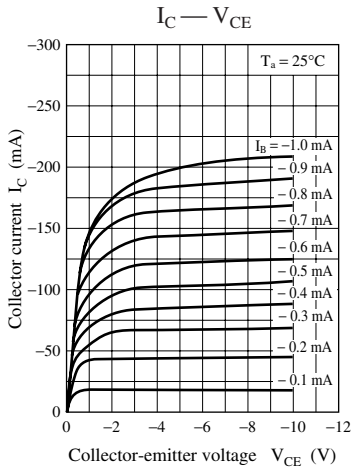
Common characteristics chart



Characteristics charts of Tr1



Characteristics charts of Tr2



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